

## KSC5321

### **High Voltage and High Reliability**

- High speed Switching
- Wide Safe Operating Area



1.Base 2.Collector 3.Emitter

## **NPN Triple Diffused Planar Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	800	V
$V_{CEO}$	Collector-Emitter Voltage	500	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	5	Α
I <sub>CP</sub>	*Collector Current (Pulse)	10	Α
I <sub>B</sub>	Base Current (DC)	2	Α
I <sub>BP</sub>	*Base Current (Pulse)	4	Α
P <sub>C</sub>	Power Dissipation(T <sub>C</sub> =25°C)	100	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

<sup>\*</sup> Pulse Test: Pulse Width = 5ms, Duty Cycle≤10%

## Thermal Characteristics $\rm T_{C}\text{=}25^{\circ}C$ unless otherwise noted

Symbol	Char	Rating	Unit	
$R_{\theta jc}$	Thermal Resistance	Junction to Case	1.25	°C/W
$R_{\theta ja}$		Junction to Ambient	62.5	

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# **Electrical Characteristics** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	800	-	-	V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 5mA, I_B = 0$	500	-	-	V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{C} = 0$	7	-	-	V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 800V, I_{E} = 0$	-	-	100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 7V, I_{C} = 0$	-	-	10	μΑ
h <sub>FE1</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.6A$	15	-	40	
h <sub>FE2</sub>		$V_{CE} = 5V, I_{C} = 3A$	8	-	-	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$	-	-	1.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$	-	-	1.5	V
f <sub>T</sub>	Current Gain bandwidth Product	$V_{CE} = 10V, I_{C} = 0.6A$	-	14	-	MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	-	65	100	pF
C <sub>ib</sub>	Input Capacitance	$V_{EB} = 7V, I_{C} = 0, f = 1MHz$	-	1400	2000	pF
t <sub>ON</sub>	Turn ON Time	$V_{CC} = 125V, I_{C} = 1A$	-	-	0.5	μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -I_{B2} = 0.2A$		-	6.5	μs
t <sub>F</sub>	Fall Time	$R_L = 125\Omega$	-	-	0.3	μs
t <sub>ON</sub>	Turn ON Time	$V_{CC} = 250V, I_{C} = 4A$	-	-	0.5	μs
t <sub>STG</sub>	Storage Time	$I_{B1} = 0.8A, I_{B2} = -1.6A$	-	-	3.0	μs
t <sub>F</sub>	Fall Time	$R_L = 62.5\Omega$	-	-	0.3	μs

# **Typical Characteristics**

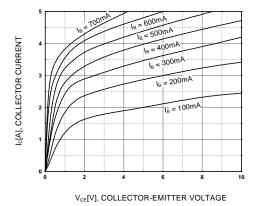


Figure 1. Static Characteristic

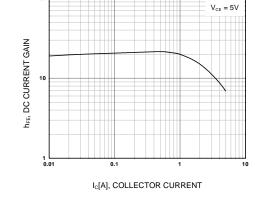


Figure 2. DC current Gain

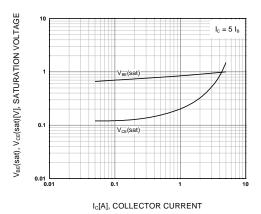


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

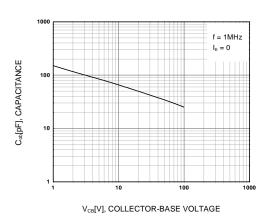


Figure 4. Collector Output Capacitance

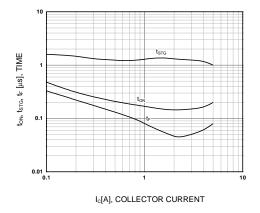


Figure 5. Switching Time

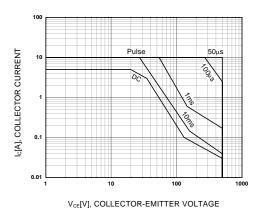


Figure 6. Safe Operating Area

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# **Typical Characteristics** (Continued)

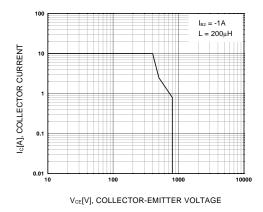


Figure 7. Reverse Bias Safe Operating Area

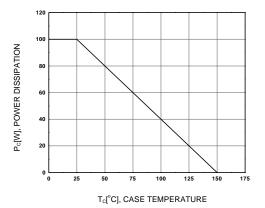
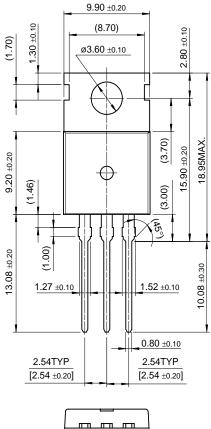
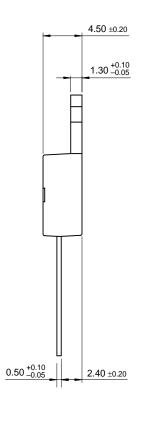


Figure 8. Power Derating

# **Package Demensions**

# TO-220





10.00 ±0.20

Dimensions in Millimeters

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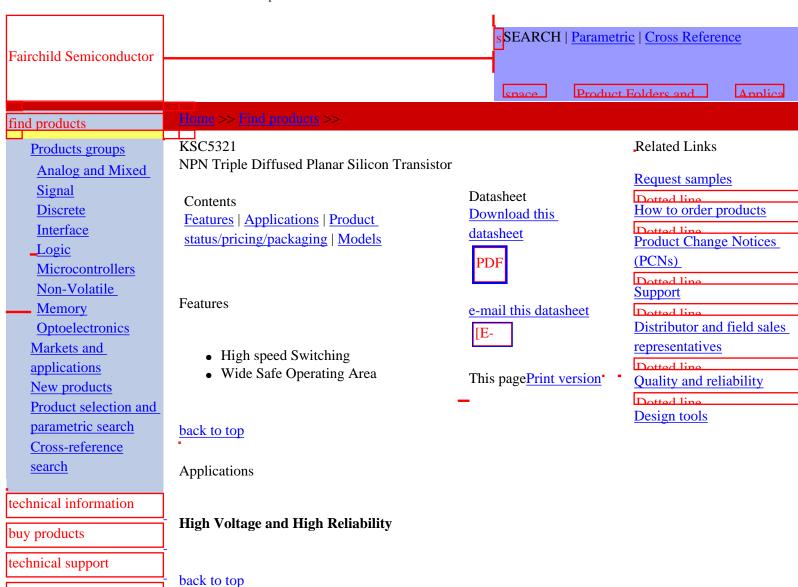
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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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Product	Product status	Pricing*	Package type	Leads	Packing method
KSC5321ATU	Full Production	N/A	TO-220	3	RAIL
KSC5321TU	Full Production	\$0.62	TO-220	3	RAIL
KSC5321	Full Production	\$0.62	TO-220	3	BULK

<sup>\* 1,000</sup> piece Budgetary Pricing

Product status/pricing/packaging

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### Models

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Package & leads	Condition	Temperature range	Software version	<b>Revision date</b>
PSPICE				
TO-220-3	Electrical/Thermal	-25°C to 100°C	9.2	Mar 16, 2001

Product Folder - Fairchild P/N KSC5321 - NPN Triple Diffused Planar Silicon Transistor

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